Memorandum

PARAMAX
A Unisys Company

PPM-93-059

DATE:

May 26, 1993

B. Fafaul/311

TO: FROM:

K. Sahu/300.1

SUBJECT:

Radiation Report on FAST/MU3

SUBJECT: Radiación

Part No. 5962-8670404PA ((UC1845J/883)

Control No. 7342

cc:

R. Kolecki/740.4

T. Miccolis/300.1 A. Sharma/311

Library/300.1 E. Bentley/740.4 SMEX, PPM File

A radiation evaluation was performed on UC1845J/883 (Pulse Width Modulator) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation levels were 5, 10, 20, 40 and 60 krads*. After 60 krads, parts were annealed at 25°C for 168 hours. The irradiation was then continued to 100 krads (cumulative). The dose rate was between 0.24 and 1.82 krads/hour, depending on the total dose level (see Table II for radiation schedule). Finally the parts were annealed for 168 hours at 100°C. After each radiation exposure and annealing treatment, parts were electrically tested according to the test conditions and the specification limits** listed in Table III.

All ten parts passed initial (pre-rad) electrical tests. All eight irradiated parts passed all electrical tests at each irradiation and annealing level up to and including the 40-krad irradiation. After the 60-krad irradiation, one part (S/N 78) read marginally below the minimum specification limit of 4.95 V for V_ref, with a reading of 4.947 V. All other irradiated parts passed all tests at this radiation level.

^{*}The term rads, as used in this document, means rads(silicon). All radiation levels cited are cumulative.

^{**}These are manufacturers' non-irradiated data specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

After annealing for 168 hours at 25°C, all irradiated parts recovered to within specification limits. Upon continued irradiation to 100 krads (cumulative), four parts (S/N 72, 73, 78 and 79) marginally fell below the minimum specification limit of 4.95 V for V_ref with readings ranging from 4.938 to 4.948 V. In addition, one part (S/N 71 marginally read below the minimum specification limit of 7.80 V for V_START, with a reading of 7.77 V. All other irradiated parts passed all tests at this radiation level.

After a final annealing at 100°C, no rebound effects were observed. All irradiated parts passed all other functional and electrical tests throughout all irradiation and annealing steps. No significant sensitivity to radiation was observed in any other test parameter.

Table IV provides a summary of the functional test results, as well as the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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TABLE I. Part Information

Generic Part Number:

UC1845J/883

Part Number:

5962-8670404PA*

FAST/MU3

Control Number:

7342

Charge Number:

C33178

Manufacturer:

Unitrode

Lot Date Code:

9252

Quantity Tested:

10

Serial Numbers of

Radiation Samples:

71, 72, 73, 74, 75, 77, 78, 79

Serial Numbers of

Control Samples:

70, 76

Part Function:

Current Mode Pulse Width Modulator

Part Technology:

CMOS

Package Style:

8-pin DIP

Test Equipment:

MARS T

Test Engineer:

T. Scharer

^{*} No radiation tolerance/hardness was guaranteed by the manufacturer for this part.

TABLE II. Radiation Schedule for UC1845

EVENTS	DATE
1) INITIAL ELECTRICAL MEASUREMENTS	04/26/93
2) 5 KRAD IRRADIATION (0.25 KRADS/HOUR) POST-5 KRAD ELECTRICAL MEASUREMENT	04/26/93 04/27/93
3) 10 KRAD IRRADIATION (0.24 KRADS/HOUR) POST-10 KRAD ELECTRICAL MEASUREMENT	04/27/93 04/27/93
4) 20 KRAD IRRADIATION (0.48 KRADS/HOUR) POST-20 KRAD ELECTRICAL MEASUREMENT	04/28/93 04/29/93
5) 40 KRAD IRRADIATION (0.90 KRADS/HOUR) POST-40 KRAD ELECTRICAL MEASUREMENT	04/29/93 04/30/93
6) 60 KRAD IRRADIATION (0.30 KRADS/HOUR) POST-60 KRAD ELECTRICAL MEASUREMENT	04/30/93 05/03/93
7) 168 HOUR ANNEALING @25°C POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENT	05/03/93 05/10/93
8) 100 KRAD IRRADIATION (1.82 KRADS/HOUR) POST-100 KRAD ELECTRICAL MEASUREMENT	05/10/93 05/11/93
9) 168 HOUR ANNEALING @100°C* POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENT	05/12/93 05/19/93

ALL ELECTRICAL MEASUREMENTS WERE PERFORMED AT 25°C.

PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS; SEE FIGURE 1.

*High temperature annealing is performed to accelerate long term time dependent effects (TDE), namely, the "rebound" effect due to the growth of interface states after the radiation exposure. For more information on the need to perform this test, refer to MIL-STD-883D, Method 1019, Para. 3.10.1.

Table III. Electrical Characteristics of UC1845

TEST	CONDITIONS	LI	MIT	UNITS
		Min	Max	
ISTART	Vcc=7.8V		1	mA
Icc	Vcc=15.0V	-	17	mA
	REFERENCE SECTION:			
v_{REF}	I _{OUT} = 1.0mA	4.95	5.05	v
V _{LINE}	12V < V _{CC} < 25V		20	mV
V _{LOAD}	lmA < I _{OUT} < 20mA		25	mV
	ERROR AMP SECTION:			
VIN	$V_{COMP} = 2.5V$	2.45	2.55	V
A _{VOL}	2.0V < V _{COMP} < 4.0V	65		dB
PSRR	$12V < V_{CC} < 25V, V_{COMP} = 2.5V$	60		đВ
I_{FB}	$V_{COMP} = 2.5V$, $R_S = 100K$ OHM	-1		uA
^I SINK	$V_{FB} = 2.7V, V_{COMP} = 1.1V$	2.0		mA
ISOURCE	$V_{FB} = 2.3V, V_{COMP} = 5.0V$		-0.5	mA
V _{OH}	IOUT = -333.3uA	5.0		V
VOL	IOUT = 260uA		1.1	V
	SENSE AMP SECTION:			
GAIN	0.0V < V _{ISENSE} < 0.8V Note:1	2.85	3.15	V/V
VSENSE	V _{COMP} = 5.0V Note:2	0.9	1.1	v
ISENSE	V _{ISENSE} = 0.0V, Rs = 100K OHM	-10		uA

Table III. Electrical Characteristics of UC1845 (cont.)

TEST	CONDITIONS	LII	TIM	UNITS
		Min	Max	
	OUTPUT SECTION:			
VoL	IOUT = 20mA		0.4	v
V _{OL}	IOUT = 200mA		2.2	V
v _{OH}	IOUT = -20mA	13		v
v _{OH}	IOUT = -200mA	12		v
	UNDER VOLTAGE LOCKOUT SECTION			
v_{TH}		7.8	9.0	V
V _{MIN}	AFTER TURN-ON	7.0	8.2	V
	AC Electrical Characteristics			
	OUTPUT SECTION:			
DELAYtd	VFB OV, V _{ISENSE} = 2V STEP		300	nS
Trise			150	nS
^T fall		_	150	nS
	PWM SECTION:			
Freq	Oscillator Accuracy	47	57	KHz
DutyCyc	Maximum Duty Cycle	46	50	8
DutyCyc	Minimum Duty Cycle		0	*

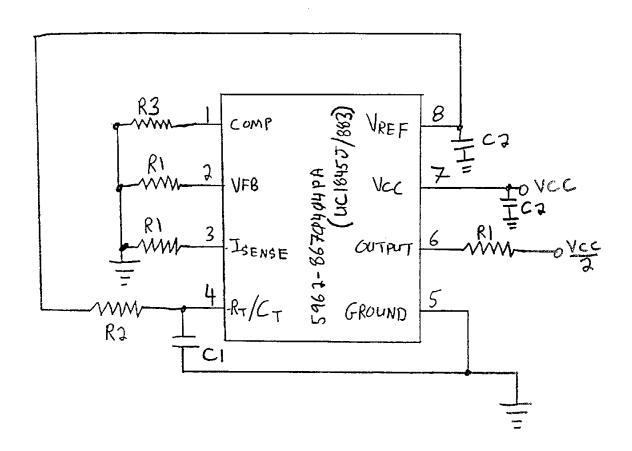
TABLE IV: Summary of Electrical Measurements After Total Dose Exposures and Annealing for UC1845 1/

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An	168	@	mean	0.44	12.9	4.97	1.27	90.0	2.50	86.2	8.68	-0.2	6.93	6 0-	5.66	0.84	3.02	0.99	-10	0.10	1.81	13.5	12.9	80.8	7.47	188	35.7	33.7	55.2	48	0
ы	0	дs	sd	.01	. 22	.01	.03	.03	.01	7.7	89.	.02	.19	.04	.01	0	.02	.01	.07	0	.01	.01	.05	.11	60.	54	2.2	1.1	.46	0.1	0
TD	10	kra	ean	.44	2.7	9.5	. 28	.07	67.	7.8	9.0	0.3	88	6.0	.64	. 84	.02	96.	-10	.10	08.	3.5	3.0	.93	.37	164	5.7	0.2	8.5	48	0
la1	r.s	 	sd m	01 0	21 1	01 4	01 1	040	01 2	6	6 0	02 -	20 6	03 -	01 5	0	01 3	0.1.0	60	0	03	01 1	14 1	11 7	09 7	54	. 3	1 3	46 5	<u></u>	0
Anne	Ч 89	@25°	āП	44	6.	. 76	25	90	50	.2	.8	. 2	94	0.	65	84	03	99	10	10	82.	Ŋ	6	07	46	0.8	. 5	1.4	4.	0	0
			d me	1 0.	1 12	1 4	1 1.	2 0.	1 2.	9 92	06 6	2 -0	0	4 -0	1 5.	0	1 3.	0.	7	0	2 1.	1 13	8 12	1 8	9	3 18	7 35	0 34	7 55	1 4	
3)	9		Ω S	4 .0	8	0.9	0.	0.9	0 6	4 7.	1. 7	2 0	6 . 2	0.	5	4 0	2 0	8	0.0	0	0.0	5 0	1 .0	6 .1	0	<u>ک</u>	1,	4 1.	4	0	0
krad			шеа	0.4	12.	4.9	1.2	0.0	2.4	93.	90.	-0-	6.9	0	5.6	0.8	3.0	0.9	-1(0.1	1.8	13.	13.	8.0	7.4	17	35.	34.	55.	48	0
E) (4.0		Вđ	.01	. 20	.01	.02	.04	.01	3.4	1.92	.02	.20	.04	.01	0	.01	.01	.10	0	.02	0	.03	.10	60.	52	2.1	1.0	.47	.08	0
(TD)			теап	0.45	13.0	4.98	1.27	90.0	2.50	90.2	90.4	-0.2	6.95	6.0-	5.65	0.84	3.02	0.99	-10	0.10	1.79	13.5	13.1	8.19	7.53	187	34.7	34.2	55.2	48	0
sure	0		S.G.	φ	.20	.01	.04	.03	.01	6.7	.72	.02	٠ ي ي	.03	0.1	0	.01	.01	10	ci	.03	.03	.17	.10	60.	53	2.5	.97	.48	60.	0
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			mean	0.46	13.2	5.00	1.27	0.04	2.51	91.8	90.5	-0.2	7.17	6.0-	5.68	88.0	3.02	6610	-10	60.0	1.77	13.5	13.1	8.37	7.54	214	33.4	32.7	54.5	48	0
	ial		က က	0	8	.02	.01	.04	.01	3.4	.78	.02	Ō	.03	.02	0	0	0	60.	0	.02	0	0.1	.08	.07	54	2.1	1.1	.54	.08	С
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			Parameters	I_START	ICC	V_REF	V_LINE	V_LOAD	V_IN	A_VOL	PSRR	I_FB	I_SINK	I_SOURCE	V_OH	V_0L	NSE	N	I_SENSE	VOL_20mA	VOL_200mA	∨ОН_20щА	100	V_TH	V_MIN	Delay_td	RISE_TIME	FALL TIME	OSC_FREQ	MAX-DUTY	MIN DUTY

in this testing. The control samples remained constant throughout the testing and are not 1/ The mean and standard deviation values were calculated over the eight parts irradiated included in this table.

irradiation limits were provided by the manufacturer at the time the tests were performed. 2/ These are manufacturers non-irradiated data sheet specification limits. No post-Radiation-sensitive parameters were V_REF and V_START.

Figure 1. Radiation Bias Circuit for UC1845



- 1) $Vcc = +15.0 \ VDC \pm 5\%$
- 2) $R_1 = 1K \text{ Ohms } \pm 10\%, 1/2 \text{ W minimum}$ $R_2 = 10K \text{ Ohms } \pm 10\%, 1/2 \text{ W minimum}$ $R_3 = 100K \text{ Ohms } \pm 10\%. 1/2 \text{ W minimum}$ $C_1 = 0.022 \text{ uF } \pm 10\%, 50V \text{ minimum}$